

• General Description

It combines advanced trench MOSFET technology with a low resistance package to provide extremely low  $R_{DS(ON)}$ .

• Features

- Low  $R_{DS(ON)}$  to minimize conductive loss
- High GOX reliability
- Low Thermal resistance

• Application

- BLDC Motor driver
- DC-DC
- Battery protection

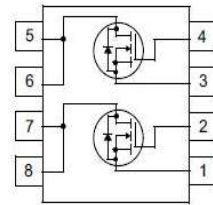
• Ordering Information:

Part NO.	ZMD68103S
Marking	ZMD68103
Packing Information	REEL TAPE
Basic ordering unit (pcs)	4000

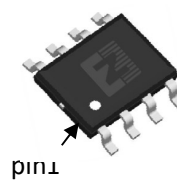
• Absolute Maximum Ratings ( $T_C=25^\circ\text{C}$ )

Parameter	Symbol	Conditions	Value	Unit
Drain-Source Voltage	$V_{DS}$		100	V
Gate-Source Voltage	$V_{GS}$		$\pm 20$	V
Continuous Drain Current	$I_D$	$T_C=25^\circ\text{C}$	9.3	A
	$I_D$	$T_C=75^\circ\text{C}$	7	A
	$I_D$	$T_C=100^\circ\text{C}$	6	A
Pulsed Drain Current	$I_{DM}$	Pulsed; $t_p \leq 10 \mu\text{s}$ ; $T_{mb} = 25^\circ\text{C}$ ;	37.2	A
Total Power Dissipation	$P_D$	$T_C=25^\circ\text{C}$	6	W
Total Power Dissipation	$P_D$	$T_A=25^\circ\text{C}$	1.3	W
Operating Junction Temperature	$T_J$		-55 to +150	$^\circ\text{C}$
Storage Temperature	$T_{STG}$		-55 to +150	$^\circ\text{C}$
Single Pulse Avalanche Energy	$E_{AS}$	$L=0.1\text{mH}$ , $V_{GS}=10\text{V}$ , $R_g=25\Omega$ ,	20	mJ
		$L=0.5\text{mH}$ , $V_{GS}=10\text{V}$ , $R_g=25\Omega$ ,	36	mJ
ESD Level (HBM)	CLASS 1B			

• Product Summary



$V_{DS} = 100\text{V}$   
 $R_{DS(ON)} = 24\text{m}\Omega$   
 $I_D = 9.3\text{A}$



SOP-8



**•Thermal resistance**

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	$R_{thJC}$		-	20	$^{\circ}C/W$
Thermal resistance, junction-ambient <sup>①</sup>	$R_{thJA}$		-	100	$^{\circ}C/W$
Soldering temperature	$T_{sold}$		-	260	$^{\circ}C$

**•Electronic Characteristics**

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	100			V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	1.4	1.8	2.5	V
Drain-Source Leakage Current	$I_{DSS}$	$V_{GS}=0V, V_{DS}=100V$			1.0	$\mu A$
Gate- Source Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$			100	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=12A$		24	32	$m\Omega$
		$V_{GS}=4.5V, I_D=12A$		30	42	$m\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS}=5V, I_{SD}=10A$		15		S
Diode Forward Voltage	$V_{FSD}$	$V_{GS}=0V, I_{SD}=12A$			1.3	V

**•Dynamic characteristics**

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Input capacitance	$C_{iss}$	$f=1MHz, V_{DS}=25V$	-	630	-	$\mu F$
Output capacitance	$C_{oss}$		-	283	-	
Reverse transfer capacitance	$C_{rss}$		-	28	-	
Gate Resistance	$R_g$	$f=1MHz$	-	2		$\Omega$
Total gate charge	$Q_g$	$V_{DD}=15V, I_D=20A, V_{GS}=10V$	-	12	-	nC
	$Q_g(4.5V)$		-	6	-	
Gate - Source charge	$Q_{gs}$		-	2	-	
Gate - Drain charge	$Q_{gd}$		-	3.4	-	
Turn-ON Delay time	$t_{D(on)}$	$V_{GS}=10V, V_{DS}=15V, R_G=3.3\Omega, I_D=20A$	-	6.5	-	ns
Turn-ON Rise time	$t_r$		-	5	-	ns
Turn-Off Delay time	$t_{D(off)}$		-	42	-	ns
Turn-Off Fall time	$t_f$		-	24	-	ns
Reverse Recovery Time	$t_{RR}$	$V_{DD}=20V, di_S/dt=100A/\mu s, I_S=20A$	-	72	-	ns
Reverse Recovery Charge	$Q_{RR}$		-	130	-	nC

Fig.1 Gate-Charge Characteristics

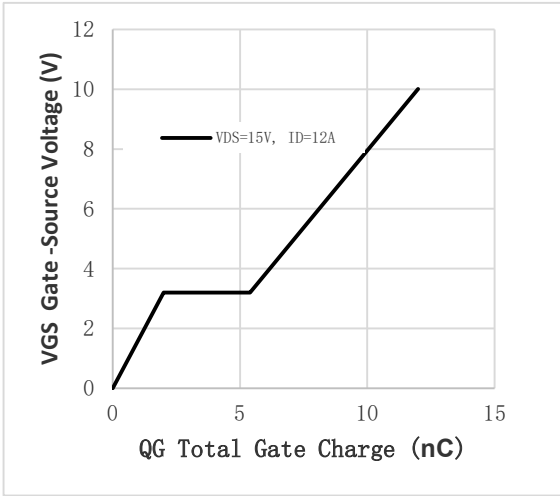


Fig.2 Capacitance Characteristics

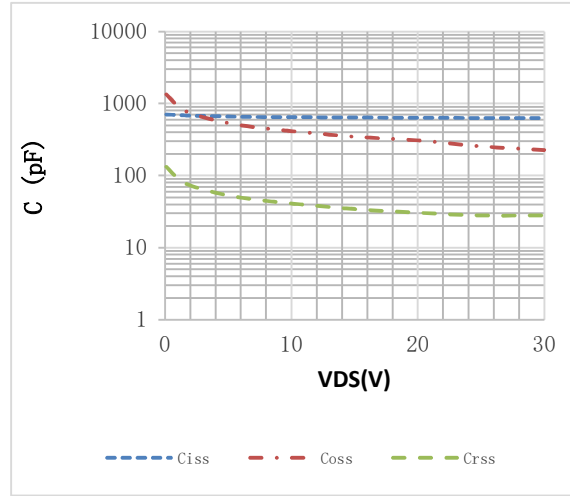


Fig.3 Power Dissipation

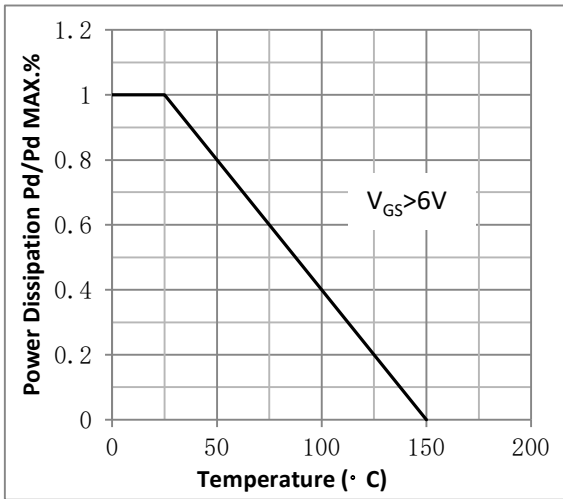


Fig.4 Typical output Characteristics

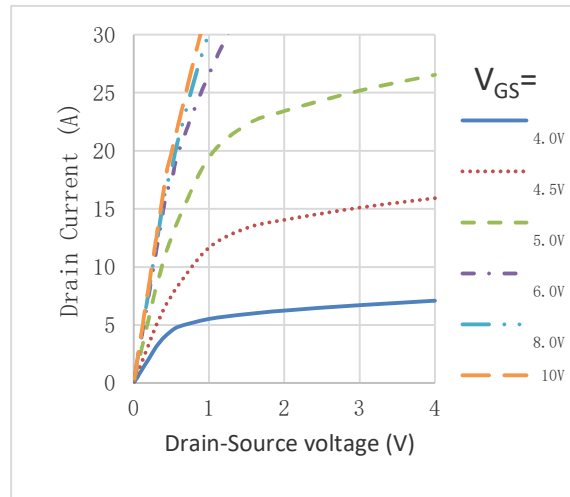


Fig.5 Threshold Voltage V.S Junction Temperature

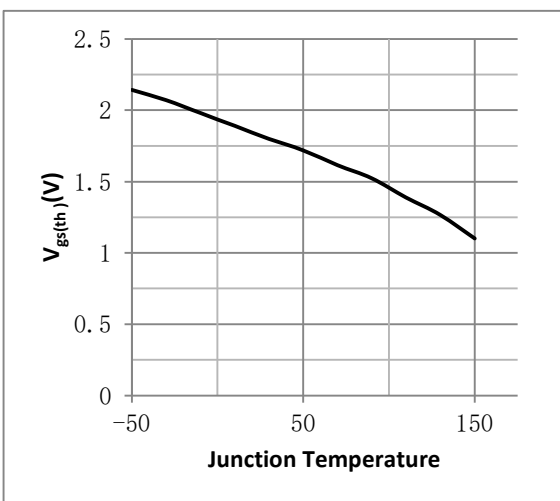


Fig.6 Resistance V.S Drain Current

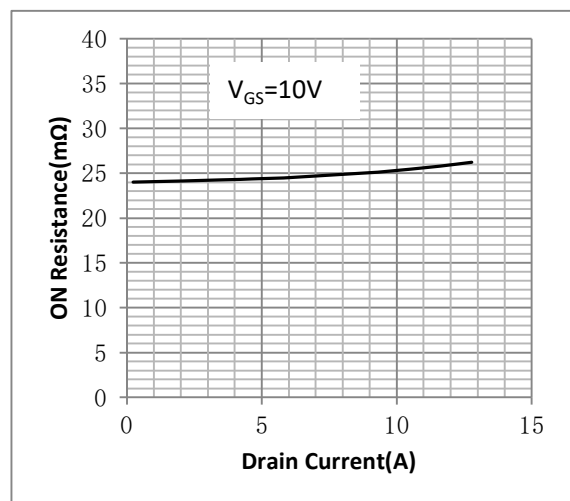


Fig.7 On-Resistance VS Gate Source Voltage

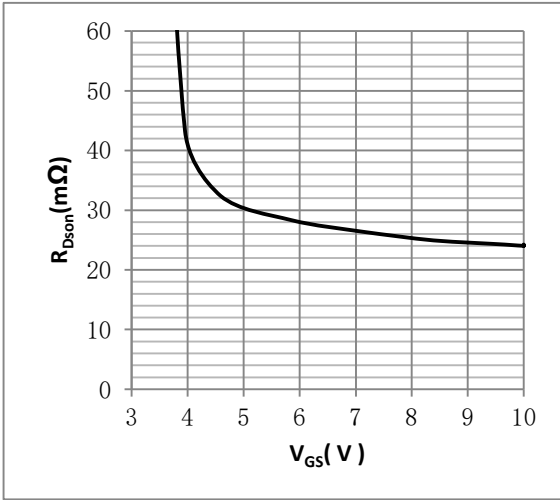


Fig.8 On-Resistance V.S Junction Temperature

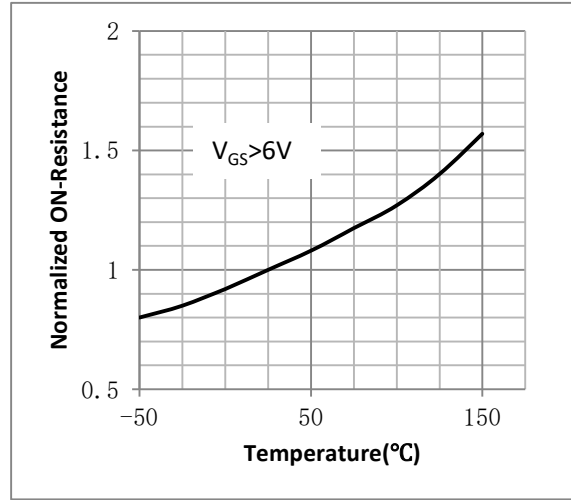


Figure 9. Diode Forward Voltage vs. Current

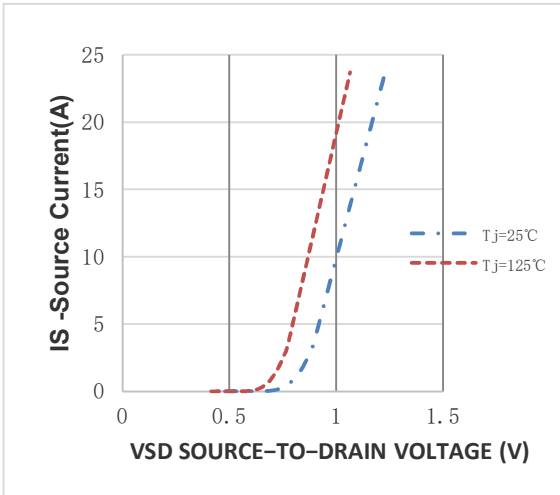


Figure 10. Transfer Characteristics

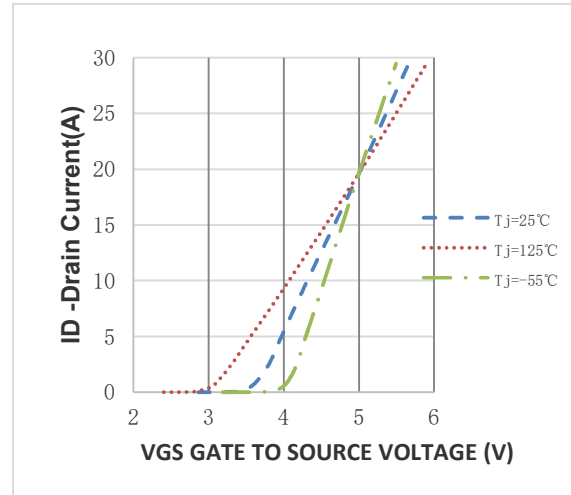


Fig.11 Safe Operating Area

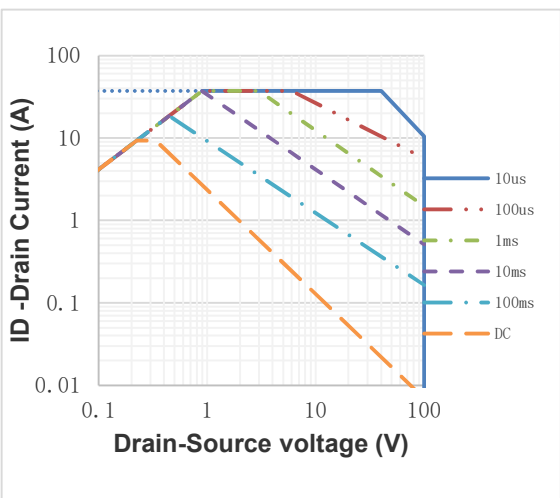
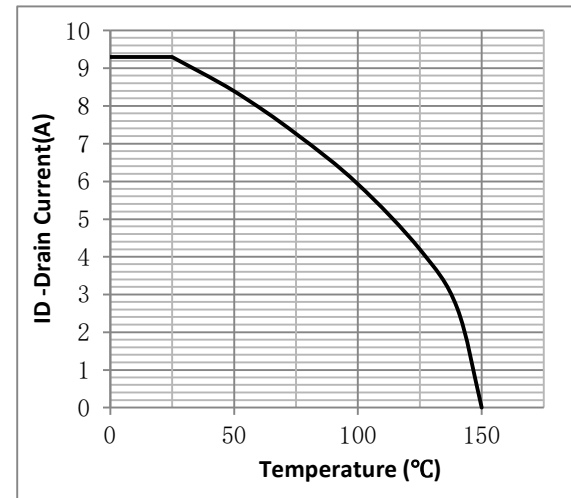
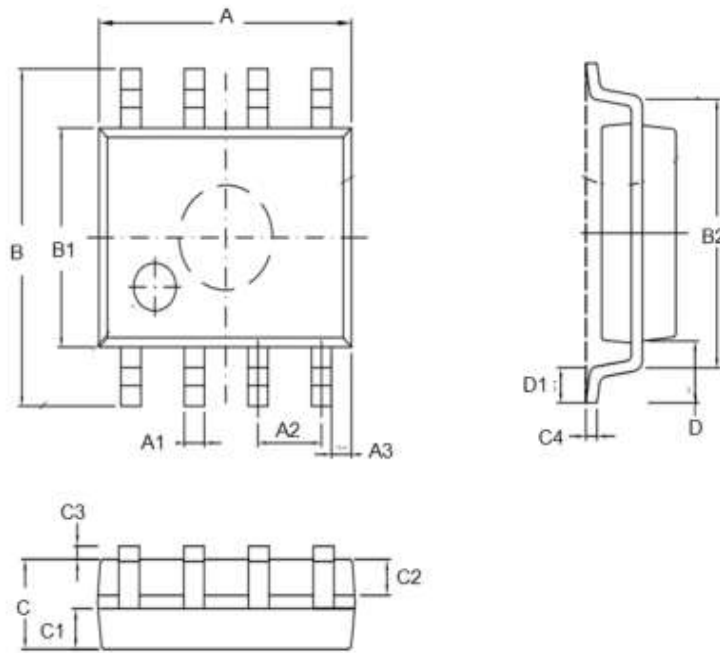


Fig.12 ID vs. Case Temperature<sup>②</sup>



●SOP-8 Package Outline

SYMBOL	min	TYP	max	SYMBOL	min		max
A	4.8		5.25	C	1.3		1.75
A1	0.37		0.49	C1	0.55		0.75
A2		1.27		C2	0.55		0.65
A3		0.41		C3	0.05		0.2
B	5.8		6.2	C4	0.1	0.2	0.23
B1	3.8		4.1	D		1.05	
B2		5		D1	0.4		0.62



**Note:**

- ① Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate;
- ② Practically the current will be limited by PCB, thermal design and operating temperature. VGS=10V.

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Revision History

Version	Date	Change
A	2021.2.3	NEW
B	2022.5.5	Add 4.5V Qg
C	2022.10.12	1.Add Reach, HF figure 2.add Dynamic characteristics 3.Modify Characteristics